

MOSFET - Power, Single N-Channel, STD Gate, TCPAK1012

80 V, 0.64 mΩ, 767 A

NTBYST0D6N08X

Features

- Top-side Cooling Package for Superior Thermal Performance
- Low Q_{RR} , Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- ORing
- Power Supply Unit (PSU)
- Motor Drives
- Synchronous Rectifier

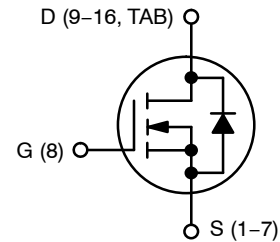
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	80	V
Gate-to-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	767	A
	$T_C = 100\text{ }^{\circ}\text{C}$		542	
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	750	W
Pulsed Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$ $t_p = 100\text{ }\mu\text{s}$	I_{DM}	2443	A
		I_{SM}	2443	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^{\circ}\text{C}$
Continuous Source-Drain Current (Body Diode)		I_S	932	A
Single Pulse Avalanche Energy ($I_{PK} = 177\text{ A}$)		E_{AS}	1566	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)		T_L	260	$^{\circ}\text{C}$

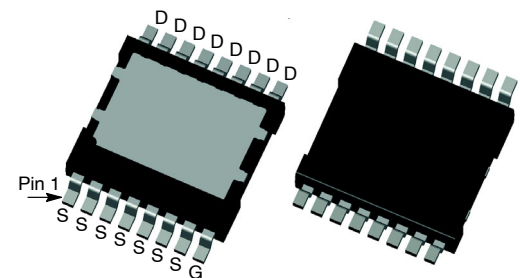
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using a 1 in², 1 oz. Cu pad
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
3. E_{AS} is based on started $T_J = 25^\circ\text{C}$, rated I_{AS} , $V_{DD} = 64 \text{ V}$, $V_{GS} = 10 \text{ V}$, 100% avalanche tested.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	0.64 mΩ @ 10 V	767 A

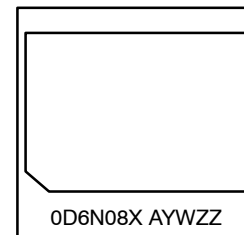


N-CHANNEL MOSFET



TCPAK1012
(TopCool)
CASE 762AA

MARKING DIAGRAM



0D6N08X = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTBYST0D6N08XTXG	TCPAK1012	1500 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Top)	$R_{\theta JC}$	0.20	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	38	
Thermal Characterization Parameter, Junction-to-Source Lead (Pin 1–7)*	Ψ_{JL}	4.1	
Thermal Characterization Parameter, Junction-to-Drain Lead (Pin 9–16)*	Ψ_{JL}	3.2	

* Low thermal conductivity test boards compliant with JEDEC Standard 51-3 for leaded surface-mount packages. 1s0p PCB board with a 1 in² copper plane, tested under natural convection conditions.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$, Referenced to 25°C		29		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}, T_J = 25^\circ\text{C}$			2.0	μA
		$V_{DS} = 80\text{ V}, T_J = 125^\circ\text{C}$			250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 80\text{ A}, T_J = 25^\circ\text{C}$		0.56	0.64	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 895\text{ }\mu\text{A}, T_J = 25^\circ\text{C}$	2.4		3.6	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 895\text{ }\mu\text{A}$		-7		mV/°C
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 80\text{ A}$		200		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance (Note 4)	C_{ISS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	8200	16419	24628	pF
Output Capacitance (Note 4)	C_{OSS}			4654	6981	
Reverse Transfer Capacitance (Note 4)	C_{RSS}			69	125	
Output Charge	Q_{OSS}			333		nC
Total Gate Charge (Note 4)	$Q_{G(TOT)}$	$V_{DD} = 40\text{ V}, I_D = 80\text{ A}, V_{GS} = 10\text{ V}$		228	342	
Threshold Gate Charge	$Q_{G(TH)}$			50		
Gate-to-Source Charge	Q_{GS}			73		
Gate-to-Drain Charge (Note 4)	Q_{GD}			35	63	
Gate Plateau Voltage	V_{GP}			4.5		V
Gate Resistance (Note 4)	R_G	$f = 1\text{ MHz}$	0.32	0.79	1.3	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}$, $V_{DD} = 40\text{ V}, I_D = 80\text{ A}$, $R_G = 2.5\text{ }\Omega$		57		ns
Rise Time	t_r			17		
Turn-Off Delay Time	$t_{d(OFF)}$			92		
Fall Time	t_f			15		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$I_S = 80\text{ A}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$		0.78	1.2	V
		$I_S = 80\text{ A}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$		0.61		

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ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SOURCE-TO-DRAIN DIODE CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}$, $I_S = 80\text{ A}$, $dI/dt = 1000\text{ A}/\mu\text{s}$, $V_{DD} = 40\text{ V}$		57		ns
Charge Time	t_a			30		
Discharge Time	t_b			27		
Reverse Recovery Charge	Q_{RR}			740		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Defined by design, not subject to production test.



TYPICAL CHARACTERISTICS

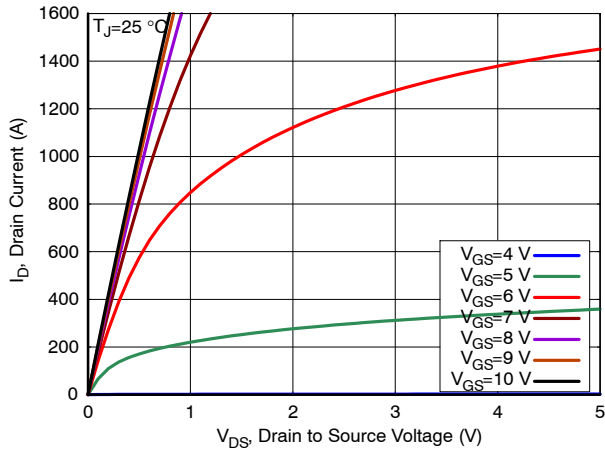


Figure 1. On-Region Characteristics

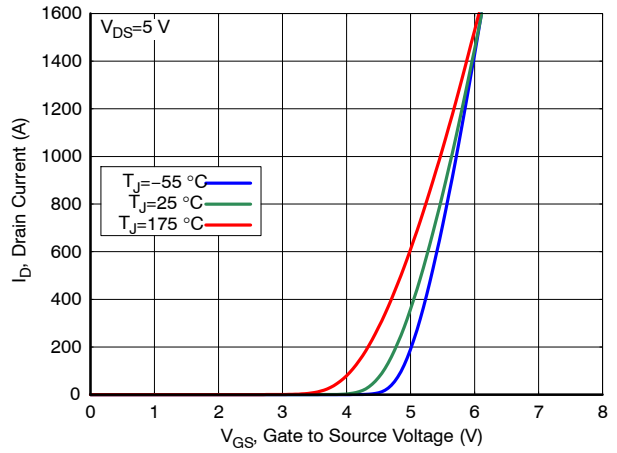


Figure 2. Transfer Characteristics

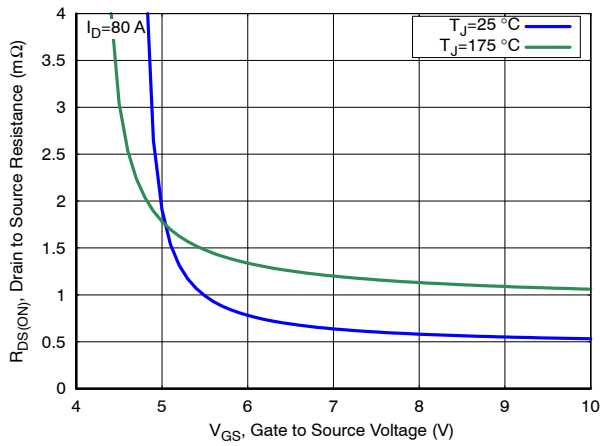


Figure 3. On-Resistance vs. Gate Voltage

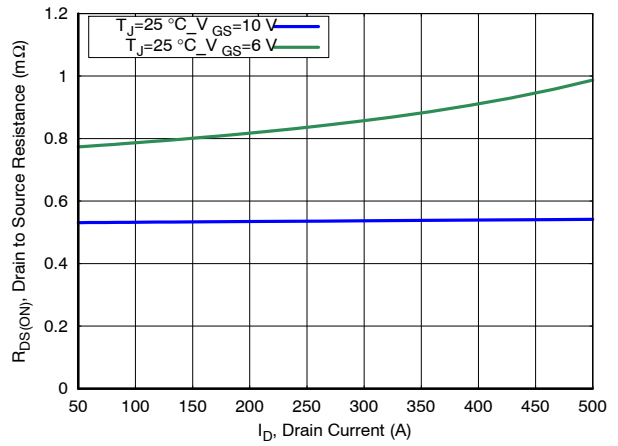


Figure 4. On-Resistance vs. Drain Current

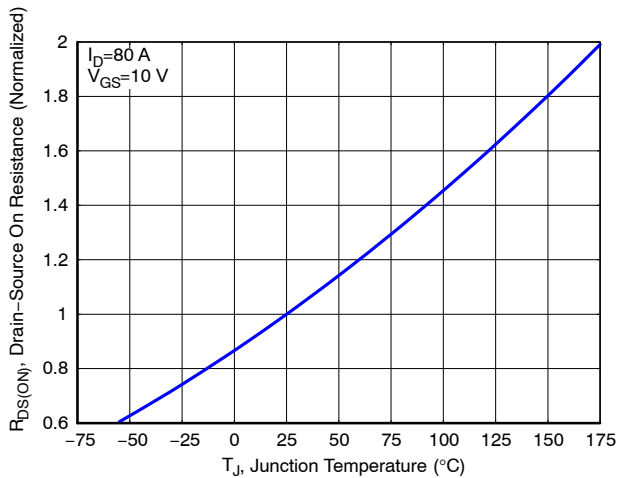


Figure 5. Normalized ON Resistance vs. Junction Temperature

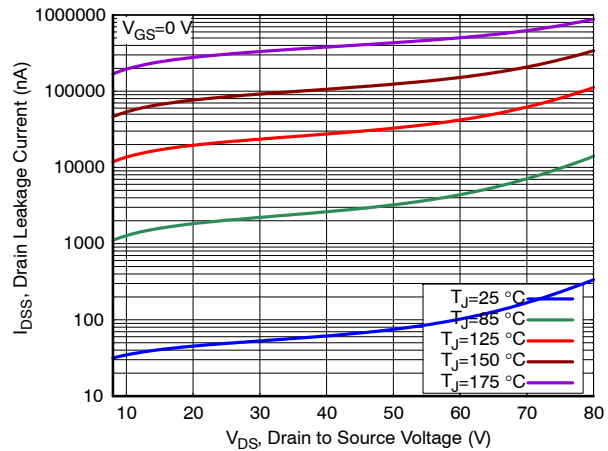


Figure 6. Drain Leakage Current vs. Drain Voltage

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TYPICAL CHARACTERISTICS

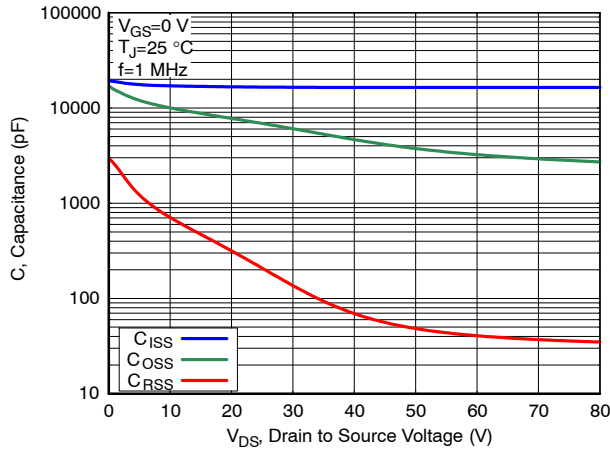


Figure 7. Capacitance Characteristics

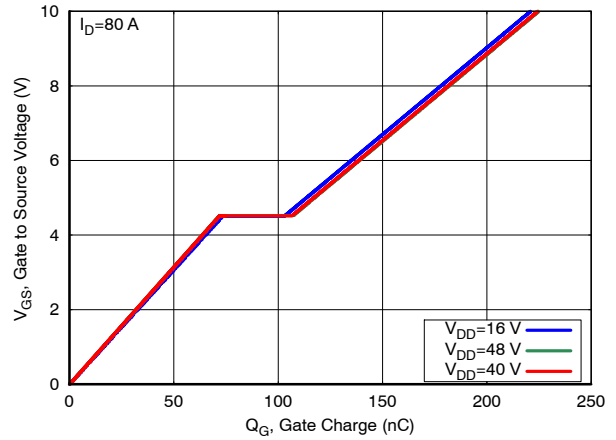


Figure 8. Gate Charge Characteristics

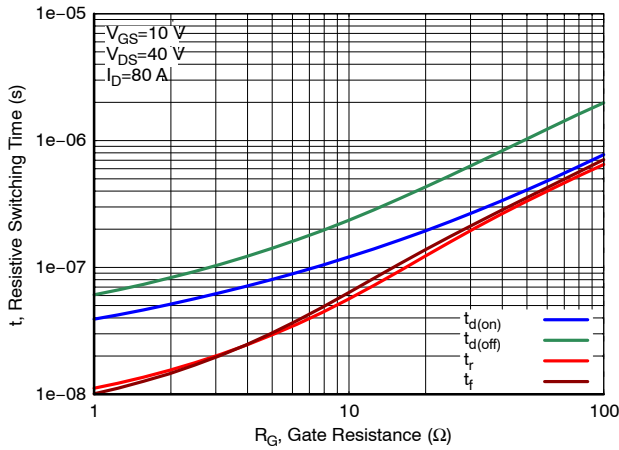


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

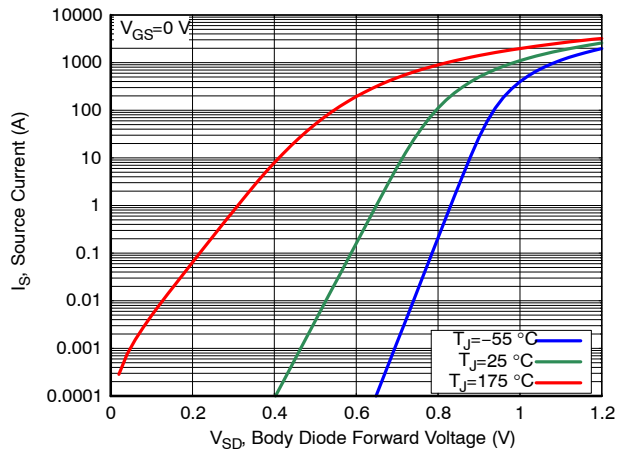


Figure 10. Diode Forward Characteristics

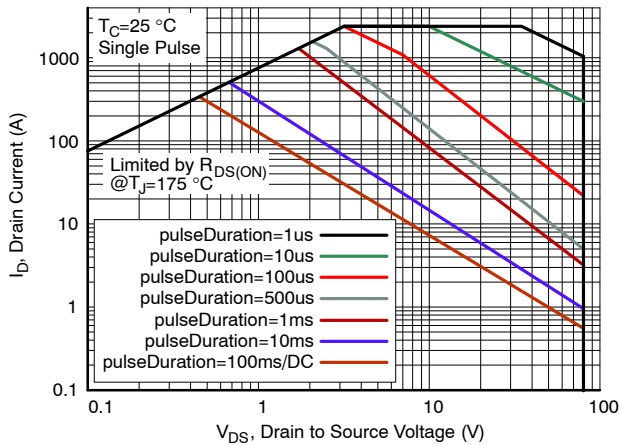


Figure 11. Safe Operating Area (SOA)

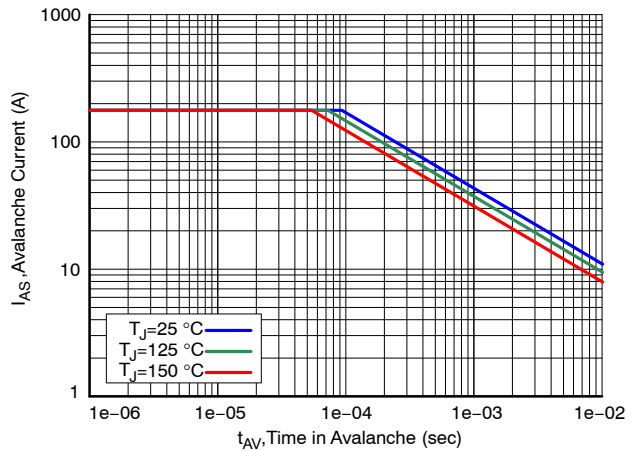


Figure 12. Avalanche Current vs. Pulse Time (UIS)

TYPICAL CHARACTERISTICS

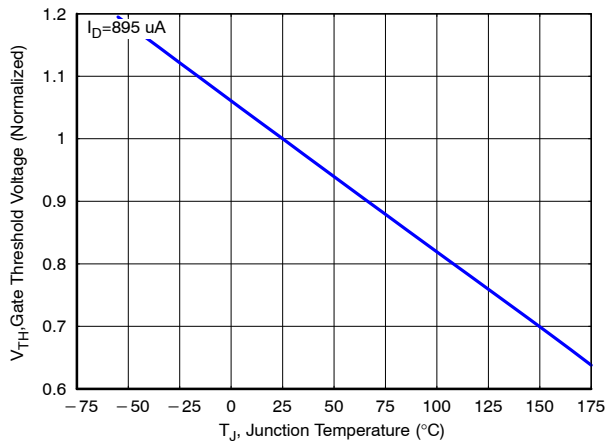


Figure 13. Gate Threshold Voltage vs Junction Temperature

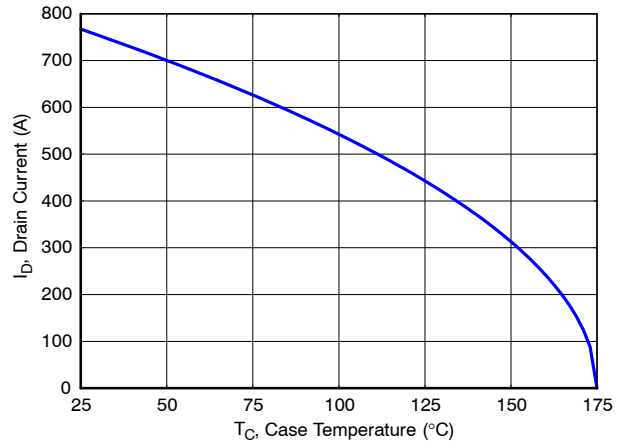


Figure 14. Maximum Current vs. Case Temperature

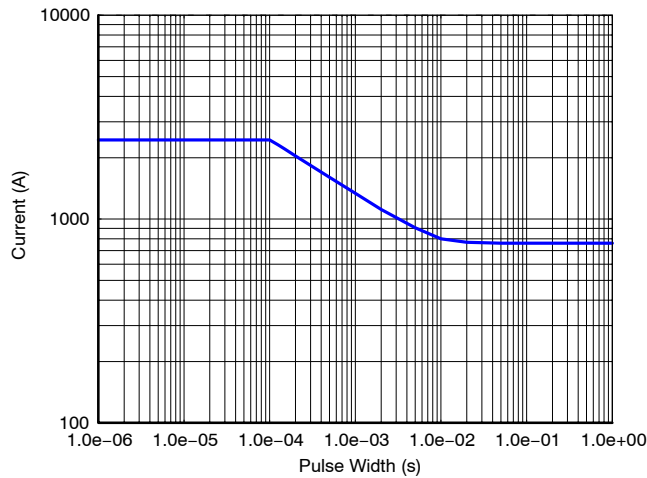


Figure 15. IDM vs. Pulse Width

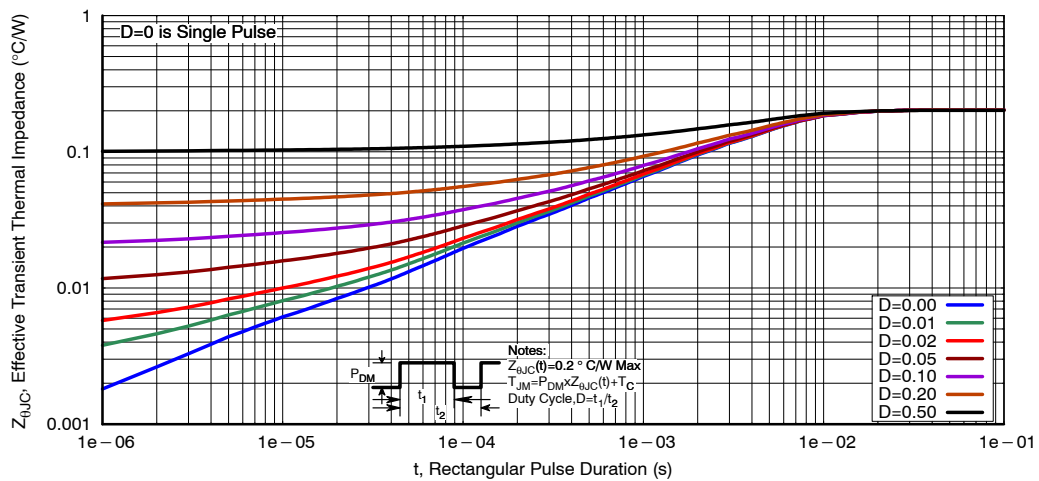


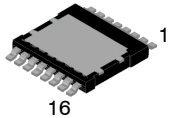
Figure 16. Transient Thermal Response

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REVISION HISTORY

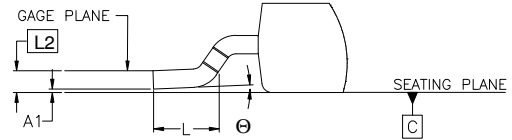
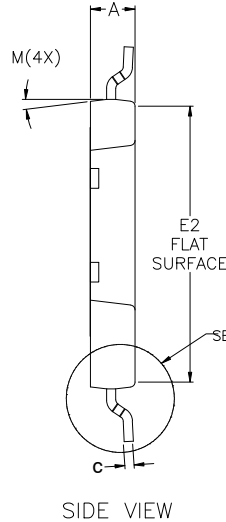
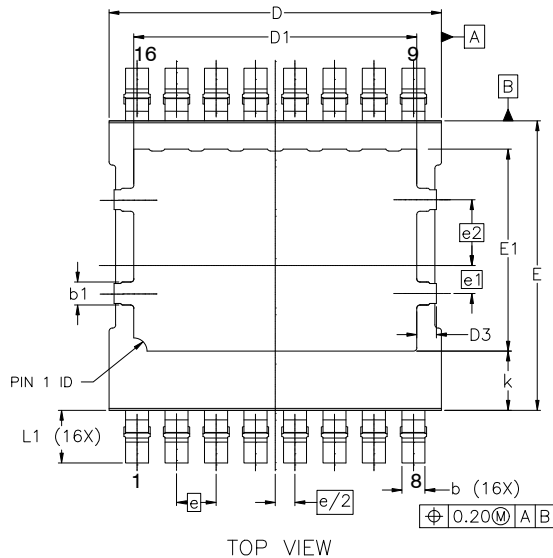
Revision	Description of Changes	Date
0	Initial document release.	7/2/2026





TCPAK16 8.80x10.10, 1.20P (TCPAK1012)
CASE 762AA
ISSUE E

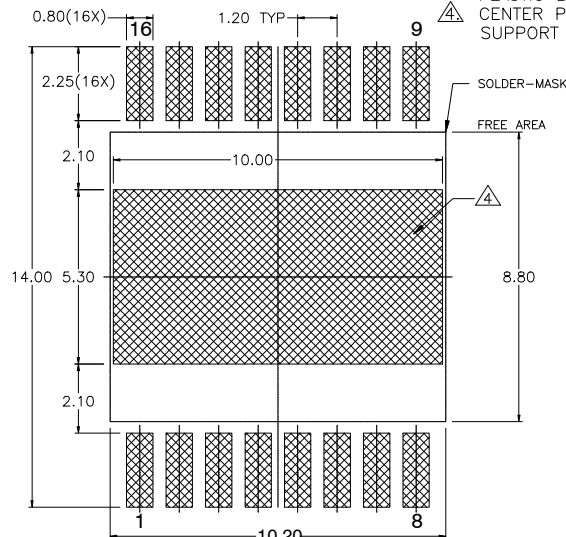
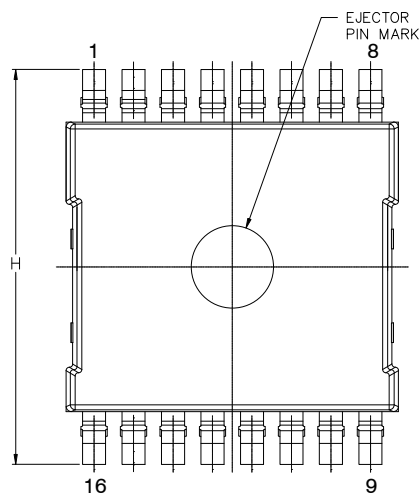
DATE 23 MAY 2025



DETAIL 'A'

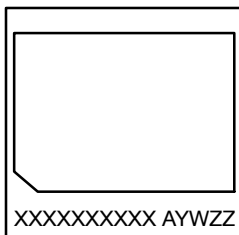
NOTES:

1. UNIT DIMENSION: MILLIMETER
 2. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR MOLD GATE REMAINS. MOLD FLASH OR GATE REMAINS SHALL NOT EXCEED 0.150mm PER SIDE.
 3. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- ⚠ CENTER PAD IS FOR PKG MECHANICAL SUPPORT ONLY. NO SOLDERING REQUIRED.



MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.30	1.35	1.40
A1	0.00	0.05	0.10
b	0.67	0.72	0.77
b1	0.65	0.70	0.75
c	0.21	0.26	0.31
D	10.00	10.10	10.20
D1	8.50	8.60	8.70
D3	0.55	0.60	0.75
E	8.70	8.80	8.90
E1	6.04	6.14	6.24
E2	---	---	8.70
e	1.20 BSC		
e/2	0.60 BSC		
e1	0.85 BSC		
e2	2.00 BSC		
k	1.70	1.80	1.90
H	11.80	12.00	12.20
L	0.80	1.00	1.20
L1	1.40	1.60	1.80
L2	0.30 BSC		
θ	---	2.5°	5°

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

LAND PATTERN RECOMMENDATION

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER: 98AON21310H

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DESCRIPTION: TCPAK16 8.80x10.10, 1.20P (TCPAK1012)

PAGE 1 OF 1

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